

LEGM25BE120E2H

IGBT Power Module

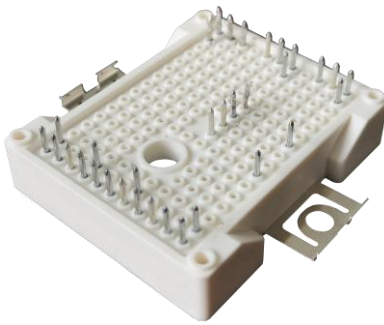
Features:

- $V_{CE}=1200V$ $I_C=25A$
- Low $V_{CE(sat)}$
- V_{CEsat} with positive temperature coefficient
- Maximum junction temperature 175°C
- Isolation Type Package

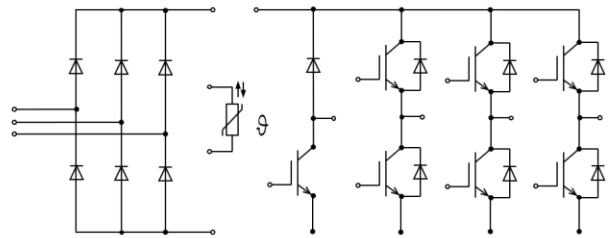
Applications:

- The inverter
- Motor control and drives

Package Type & Internal Circuit



E2



Internal Circuit

Maximum Rated Values (IGBT Inverter)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Collector-emitter voltage	$V_{EC}=0V, I_C=1mA, T_{vj}=25^\circ C$	1200	V
I_C	Continuous Collector Current	$T_C=100^\circ C$	25	A
I_{CRM}	Peak Collector Current	$I_{CRM}=2I_C$	50	A
V_{GES}	Gate-Emitter Voltage	$T_{vj}=25^\circ C$	± 30	V
P_{tot}	Total Power Dissipation	$T_C=25^\circ C, T_{vjmax}=175^\circ C$	170	W

Maximum Rated Values (IGBT Inverter)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=25\text{ A}, V_{GE}=15\text{ V}, T_{vj}=25^\circ\text{C}$		2.01		V	
		$I_C=25\text{ A}, V_{GE}=15\text{ V}, T_{vj}=150^\circ\text{C}$		2.53		V	
$V_{GE(th)}$	Gate Threshold Voltage	$I_C= 5.0\text{ mA}, V_{CE}= V_{GE}, T_{vj}= 25^\circ\text{C}$		5.8		V	
I_{CES}	Collector-Emitter Cut-off Current	$V_{CE}= 1200\text{ V}, V_{GE}=0\text{ V}, T_{vj}= 25^\circ\text{C}$			1.2	mA	
I_{GES}	Gate-Emitter Leakage Current	$V_{CE}=0\text{ V}, V_{GE}= 15\text{ V}, T_{vj}= 25^\circ\text{C}$			410	nA	
$t_{d(on)}$	Turn-on Delay Time, Inductive Load	$I_C= 25\text{ A}, V_{CE}= 600\text{ V}$ $V_{GE}= \pm 15\text{ V}$ $R_G= 20\ \Omega$ $T_{vj}= 25^\circ\text{C}$		170		ns	
t_r	Rise Time, Inductive Load			160		ns	
$t_{d(off)}$	Turn-off Delay Time, Inductive Load			170		ns	
t_f	Fall Time, Inductive Load			150		ns	
E_{on}	Turn-on Energy Loss per Pulse				3.7		mJ
E_{off}	Energy Loss per Pulse				1.4		mJ
$t_{d(on)}$	Turn-on Delay Time, Inductive Load		$I_C= 25\text{ A}, V_{CE}= 600\text{ V}$ $V_{GE}= \pm 15\text{ V}$ $R_G= 20\ \Omega$ $T_{vj}= 150^\circ\text{C}$		130		ns
t_r	Rise Time, Inductive Load				180		ns
$t_{d(off)}$	Turn-off Delay Time, Inductive Load				250		ns
t_f	Fall Time, Inductive Load				180		ns
E_{on}	Turn-on Energy Loss per Pulse				3.9		mJ
E_{off}	Energy Loss per Pulse				1.8		mJ
R_{thJC}	Thermal resistance, junction to case	per IGBT				0.89	K/W
$T_{vj\ op}$	Temperature under switching conditions		-40		150	$^\circ\text{C}$	
I_{sc}	SC	$V_{GE} \leq 15\text{ V}, V_{CE}= 600\text{ V},$ $t_p \leq 10\ \mu\text{s}, T_{vj}= 150^\circ\text{C},$ $V_{CEmax}= V_{CES}-L_{sCE} \cdot di/dt$		100		A	

Maximum Rated Values (Diode Inverter)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	$T_{vj}= 25\text{ }^{\circ}\text{C}$		1200		V
I_F	Continuous DC Forward Current	$T_C= 100\text{ }^{\circ}\text{C}$		25		A
I_{FRM}	Repetitive Peak Forward Current	$t_p= 1\text{ ms}$		50		A
I^2t	I^2t Value	$V_R= 0\text{ V}$, $t_p= 10\text{ ms}$, $T_{vj}= 150\text{ }^{\circ}\text{C}$		100		A ² s

Characteristic Values (Diode Inverter)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit	
V_F	Forward Voltage	$I_F= 25\text{ A}$, $V_{CE}= 0\text{ V}$, $T_{vj}= 25\text{ }^{\circ}\text{C}$		1.98		V	
		$I_F= 25\text{ A}$, $V_{CE}= 0\text{ V}$, $T_{vj}= 150\text{ }^{\circ}\text{C}$		1.90		V	
t_{rr}	Reverse Recovery time	$I_F= 25\text{ A}$, $V_R= 600\text{ V}$ $-di/dt= 250\text{ A/us}$		220		ns	
Q_r	Recovered Charge			0.8		uC	
E_{rec}	Reverse Recovery Energy		$T_{vj}= 25\text{ }^{\circ}\text{C}$		0.2		mJ
t_{rr}	Reverse Recovery time	$I_F= 25\text{ A}$, $V_R= 600\text{ V}$ $-di/dt= 250\text{ A/us}$		340		ns	
Q_r	Recovered Charge		$T_{vj}= 150\text{ }^{\circ}\text{C}$		1.6		uC
E_{rec}	Reverse Recovery Energy				0.5		mJ
R_{thJC}	Thermal resistance, junction to case	$I_F= 25\text{ A}$, $V_{CE}= 0\text{ V}$, $T_{vj}= 25\text{ }^{\circ}\text{C}$			1.24	K/W	
$T_{vj\text{ op}}$	Temperature under switching conditions		-40		150	$^{\circ}\text{C}$	

Maximum Rated Values (IGBT Brake-Chopper)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{CES}	Collector-emitter voltage	$T_{vj} = 25\text{ }^{\circ}\text{C}$		1200		V
I_C	Continuous Collector Current	$T_C = 100\text{ }^{\circ}\text{C}, T_{vj\text{ max}} = 175\text{ }^{\circ}\text{C}$		15		A
I_{CRM}	Peak Collector Current	$I_{CRM} = 2I_C$		30		A
V_{GES}	Gate-Emitter Voltage	$T_{vj} = 25\text{ }^{\circ}\text{C}$	-20		20	V

Characteristic Values (IGBT Brake-Chopper)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 15\text{ A}, V_{GE} = 15\text{ V}, T_{vj} = 25\text{ }^{\circ}\text{C}$		2.31		V	
		$I_C = 15\text{ A}, V_{GE} = 15\text{ V}, T_{vj} = 150\text{ }^{\circ}\text{C}$		2.52		V	
$V_{GE(th)}$	Gate Threshold Voltage	$I_C = 5.0\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25\text{ }^{\circ}\text{C}$		5.8		V	
I_{CES}	Collector-Emitter Cut-off Current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25\text{ }^{\circ}\text{C}$			1.2	mA	
I_{GES}	Gate-Emitter Leakage Current	$V_{CE} = 0\text{ V}, V_{GE} = 15\text{ V}, T_{vj} = 25\text{ }^{\circ}\text{C}$			410	nA	
$t_{d(on)}$	Turn-on Delay Time, Inductive Load	$I_C = 15\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_G = 50\text{ }\Omega$ $T_{vj} = 25\text{ }^{\circ}\text{C}$		200		ns	
t_r	Rise Time, Inductive Load			120		ns	
$t_{d(off)}$	Turn-off Delay Time, Inductive Load			290		ns	
t_f	Fall Time, Inductive Load			200		ns	
E_{on}	Turn-on Energy Loss per Pulse				2.8		mJ
E_{off}	Energy Loss per Pulse				0.8		mJ
$t_{d(on)}$	Turn-on Delay Time, Inductive Load		$I_C = 15\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_G = 50\text{ }\Omega$ $T_{vj} = 150\text{ }^{\circ}\text{C}$		200		ns
t_r	Rise Time, Inductive Load				240		ns
$t_{d(off)}$	Turn-off Delay Time, Inductive Load				320		ns
t_f	Fall Time, Inductive Load				290		ns
E_{on}	Turn-on Energy Loss per Pulse				3.2		mJ
E_{off}	Energy Loss per Pulse				1.1		mJ
R_{thJC}	Thermal resistance, junction to case	pro IGBT / per IGBT			1.1	K/W	
$T_{vj\text{ op}}$	Temperature under switching conditions		-40		150	$^{\circ}\text{C}$	

Maximum Rated Values (Diode Rectifier)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{RRM}	Repetitive peak reverse voltage	$T_{vj}= 25\text{ }^{\circ}\text{C}$		1800		V
I_{FRMSM}	Maximum RMS forward current per chip	$T_c= 80\text{ }^{\circ}\text{C}$		50		A
I_{RMSM}	Maximum RMS current at rectifier chip	$T_c= 80\text{ }^{\circ}\text{C}$		50		A
I_{FSM}	Surge forward current	$t_p=10\text{ms}$ $T_{vj}=25\text{ }^{\circ}\text{C}$		300		A
I^2t	I^2t -value			450		A ² S
I_{FSM}	Surge forward current	$t_p=10\text{ms}$ $T_{vj}=125\text{ }^{\circ}\text{C}$		230		A
I^2t	I^2t -value			310		A ² S

Characteristic Values (Diode Rectifier)

V_F	Forward voltage	$T_{vj}= 150\text{ }^{\circ}\text{C}$ $I_F= 25\text{ A}$		1.1		V
I_R	Reverse current	$T_{vj}= 150\text{ }^{\circ}\text{C}$ $V_R= 1800\text{ V}$		1.1		mA
R_{thjc}	Thermal resistance junction to case	per diode			1.1	K/W
T_{vjop}	Temperature under switching conditions		-40		150	$^{\circ}\text{C}$

Maximum Rated Values (Diode Brake-Chopper)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	$T_{vj}= 25\text{ }^{\circ}\text{C}$		1200		V
I_F	Continuous DC Forward Current	$T_C= 100\text{ }^{\circ}\text{C}$		15		A
I_{FRM}	Repetitive Peak Forward Current	$t_p= 1\text{ ms}$		30		A
I^2t	I^2t Value	$V_R= 0\text{ V}$, $t_p= 10\text{ ms}$, $T_{vj}= 150\text{ }^{\circ}\text{C}$		15		A ² s

Characteristics (Diode Brake-Chopper)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit	
V_F	Forward Voltage	$I_F= 15\text{ A}$, $V_{CE}= 0\text{ V}$, $T_{vj}= 25\text{ }^{\circ}\text{C}$		1.98		V	
		$I_F= 15\text{ A}$, $V_{CE}= 0\text{ V}$, $T_{vj}= 150\text{ }^{\circ}\text{C}$		1.90		V	
t_{rr}	Reverse Recovery time	$I_F=15\text{ A}$, $V_R= 600\text{ V}$ -di/dt= 300 A/us $T_{vj}= 25\text{ }^{\circ}\text{C}$		340		ns	
Q_r	Recovered Charge			0.8		uC	
E_{rec}	Reverse Recovery Energy				0.2		mJ
t_{rr}	Reverse Recovery time	$I_F= 15\text{ A}$, $V_R= 600\text{ V}$ -di/dt= 300 A/us $T_{vj}= 150\text{ }^{\circ}\text{C}$		400		ns	
Q_r	Recovered Charge				1.6		uC
E_{rec}	Reverse Recovery Energy				0.4		mJ
R_{thJC}	Thermal resistance, junction to case	$I_F=15\text{ A}$, $V_{CE}= 0\text{ V}$, $T_{vj}= 25\text{ }^{\circ}\text{C}$			1.75	K/W	
$T_{vj\text{ op}}$	Temperature under switching conditions		-40		150	$^{\circ}\text{C}$	

NTC-Thermistor (Characteristic Values)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
R ₂₅	Rated resistance	T _c = 25 °C		5		KΩ
ΔR/R	Deviation of R100	T _c = 100 °C	-5		5	%
P ₂₅	Power dissipation	T _c = 25 °C		20		mW
B _{25/50}	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298,15K))]$		3380		K
B _{25/100}	B-value	$R_2=R_{25}\exp[B_{25/100}(1/T_2-1/(298,15K))]$		3450		K

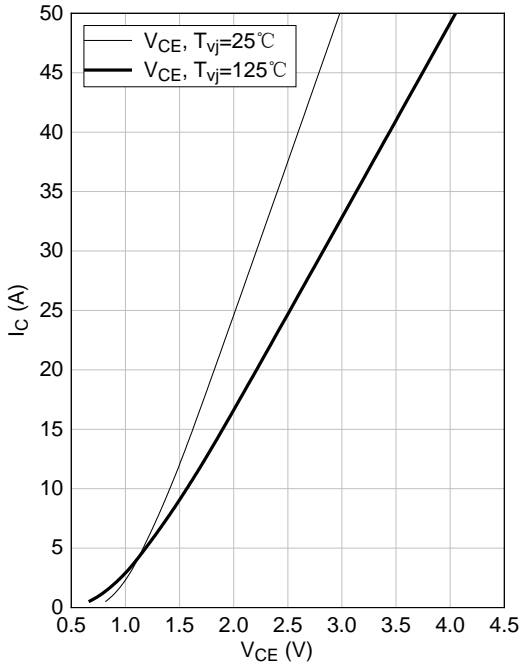
Module Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V _{isol}	Isolation voltage	t= 1 min,f= 50 Hz	2500			V
T _{stg}	Storage Temperature		-40		150	°C
F	Mounting Force per Clamp		40		80	N
G	Weight of Module			40		g

Output characteristic of IGBT, Inverter (typical)

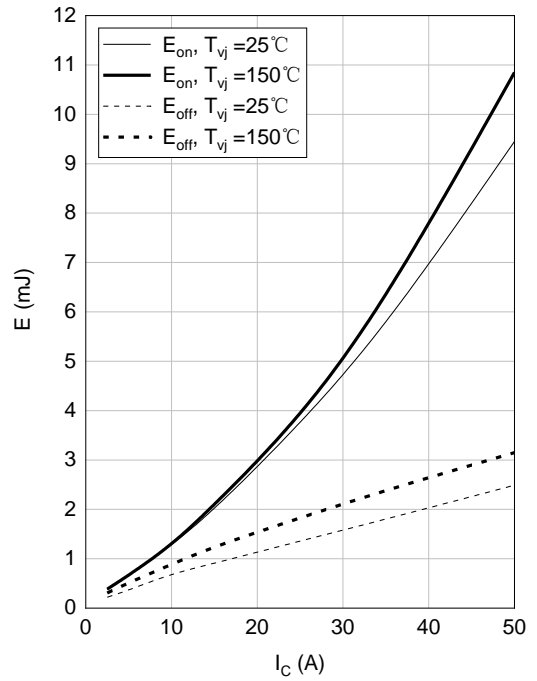
$$I_c = f(V_{CE})$$

$$V_{GE} = 15V$$


Switching losses of IGBT, Inverter (typical)

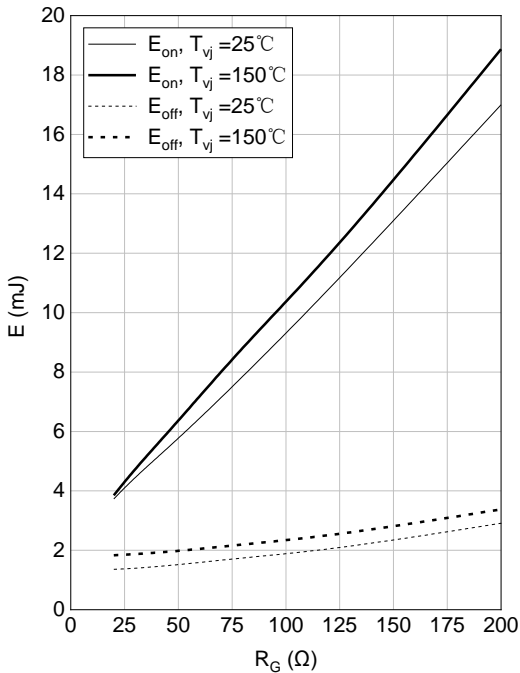
$$E_{on} = f(I_c), E_{off} = f(I_c)$$

$$V_{GE} = \pm 15V, R_G = 20 \Omega, V_{CE} = 600 V$$


Switching losses of IGBT, Inverter (typical)

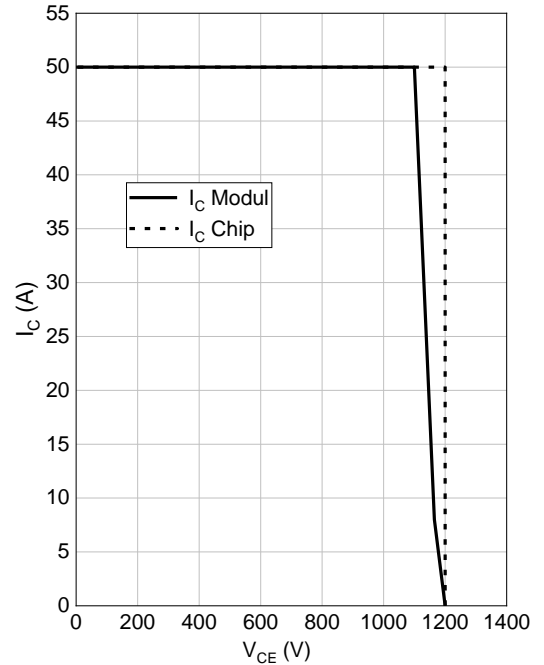
$$E_{on} = f(R_G), E_{off} = f(R_G)$$

$$V_{GE} = \pm 15 V, I_c = 25 A, V_{CE} = 600 V$$


RBSOA IGBT, Inverter (typical)

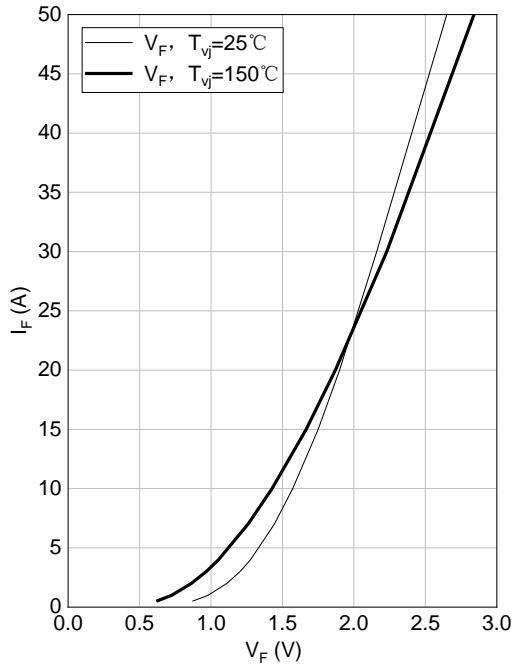
$$I_c = f(V_{CE})$$

$$V_{GE} = \pm 15 V, R_G = 20 \Omega, T_{vj} = 150^\circ C$$



Forward characteristic of Diode, Inverter (typical)

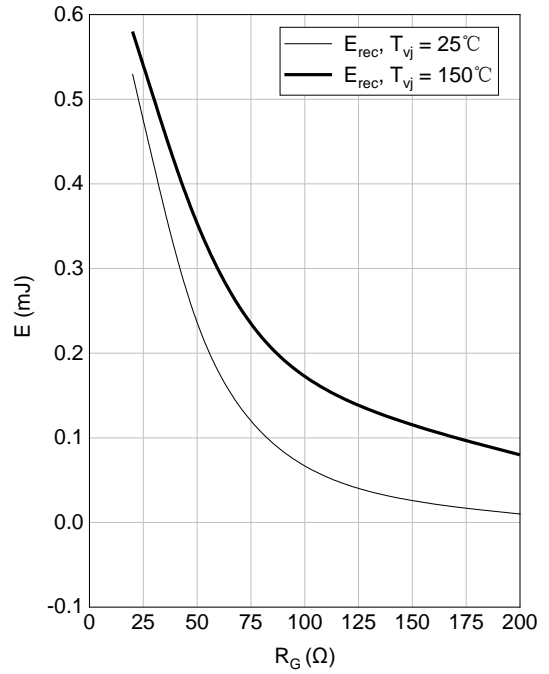
$$I_F = f(V_F)$$



Switching losses of Diode, Inverter (typical)

$$E_{rec} = f(R_G),$$

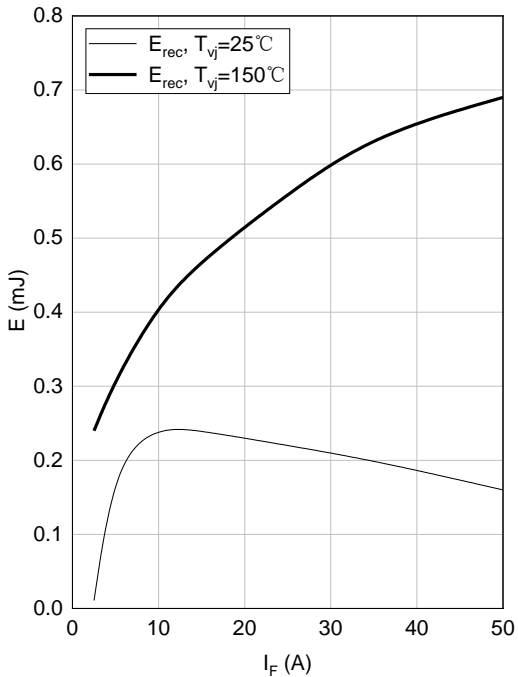
$$I_F = 25A, V_{CE} = 600V$$



Switching losses of Diode, Inverter (typical)

$$E_{rec} = f(I_F),$$

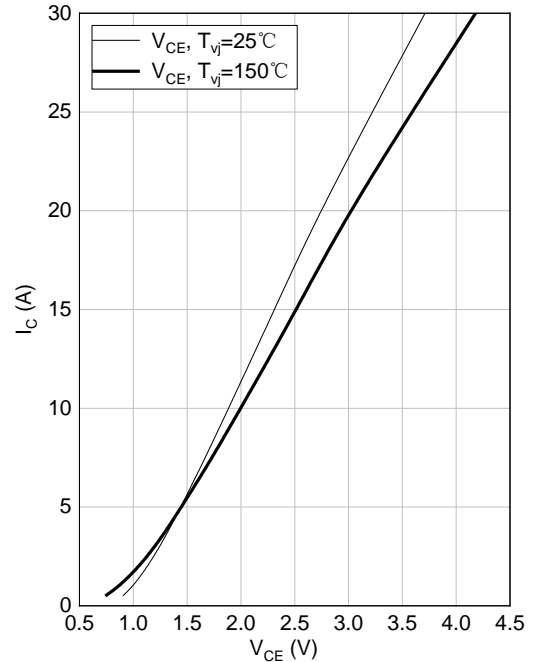
$$R_G = 20\ \Omega, V_{CE} = 600V$$



Output characteristic of IGBT, Brake-Chopper, (typical)

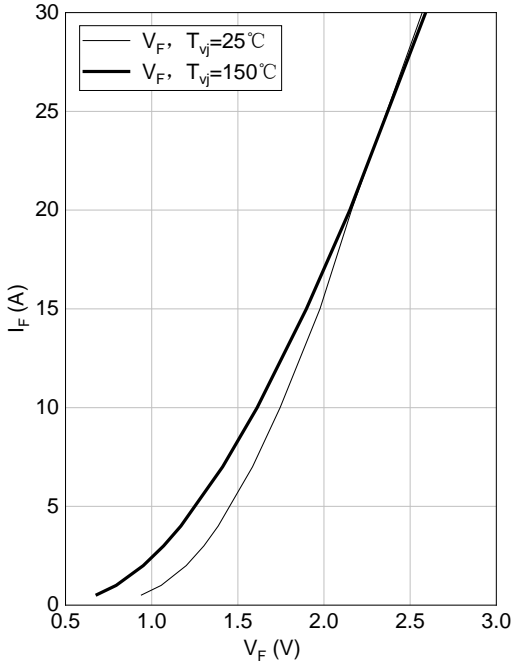
$$I_c = f(V_{CE})$$

$$V_{GE} = 15V$$



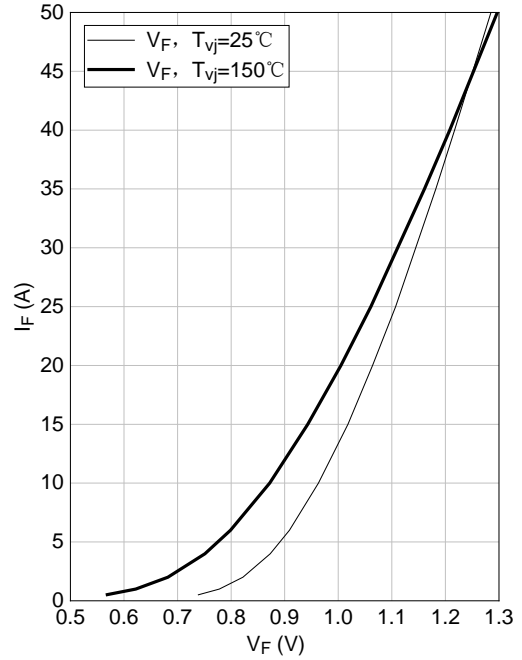
Forward characteristic of Diode, Brake-Chopper (typical)

$$I_F = f(V_F)$$



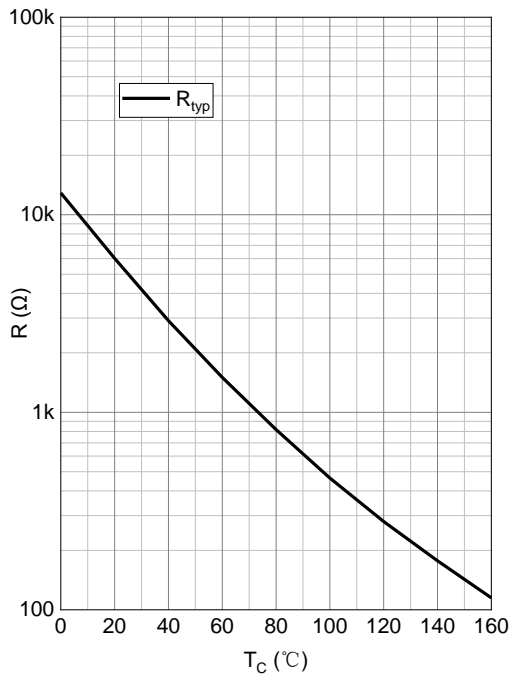
Forward characteristic of Diode, Rectifier (typical)

$$I_F = f(V_F)$$

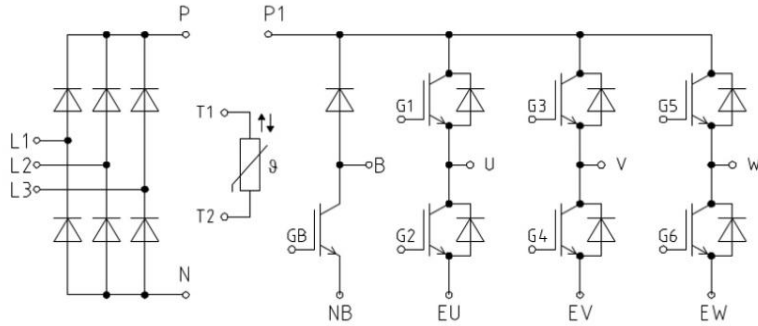


NTC-thermistor-temperature characteristic (typical)

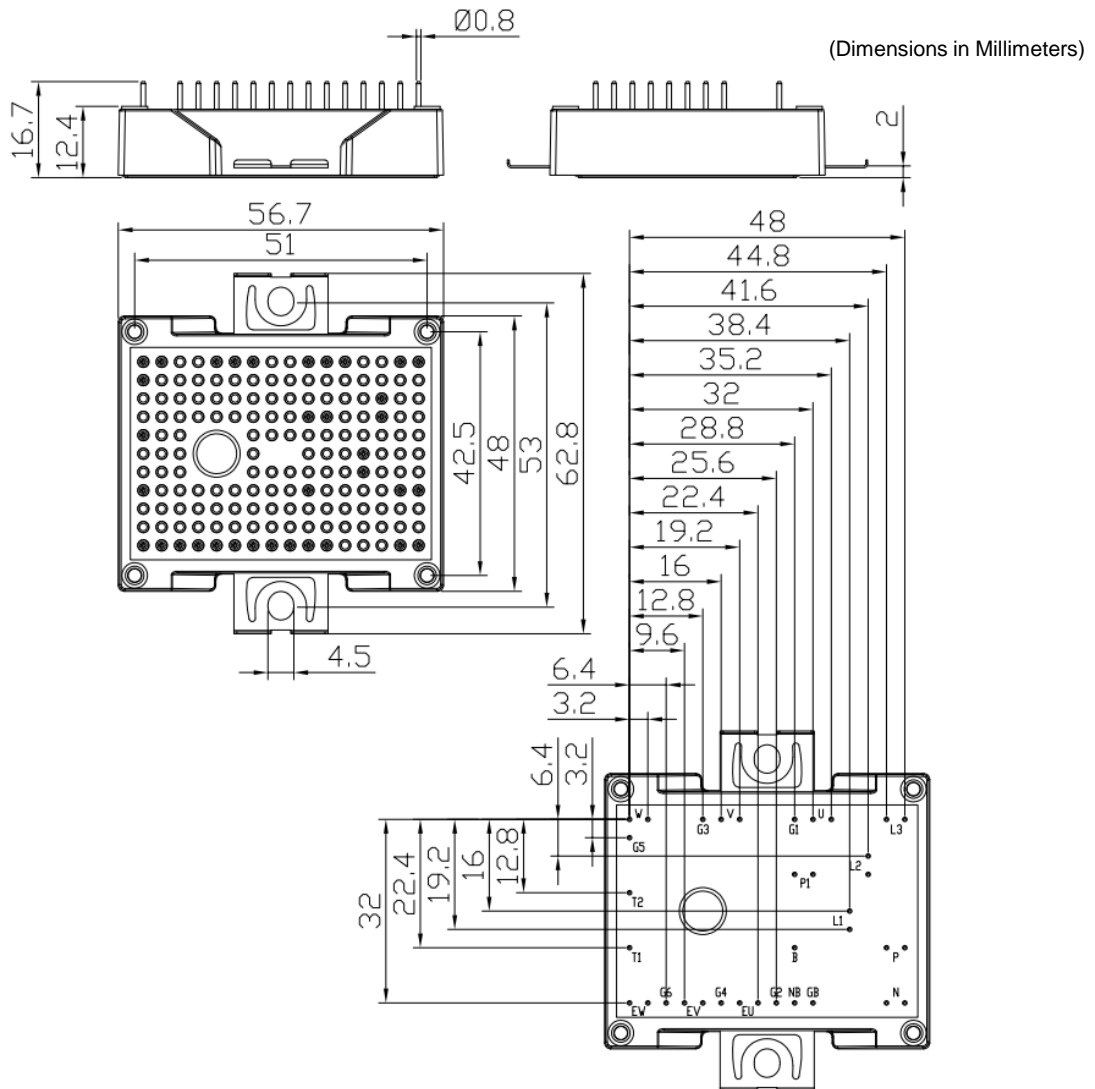
$$R = f(T_{NTC}),$$



Circuit Diagram



Package Dimensions



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